

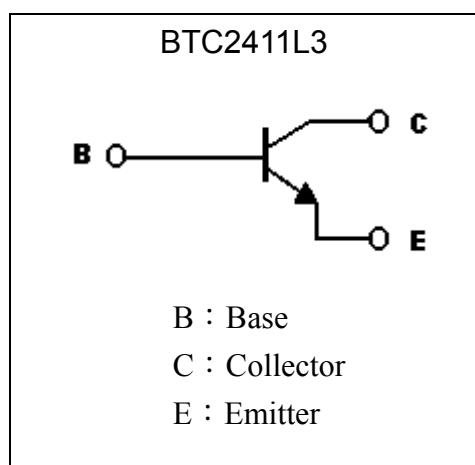
## General Purpose NPN Epitaxial Planar Transistor

# BTC2411L3

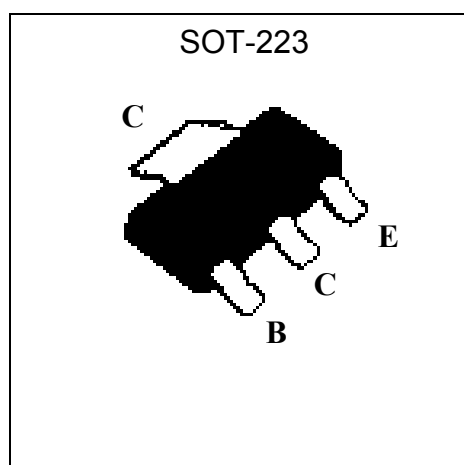
### Description

- The BTC2411L3 is designed for using in driver stage of AF amplifier and general purpose switching application.
- High  $I_{C(Max)}$ ,  $I_{C(Max)} = 0.6A$ .
- Low  $V_{CE(sat)}$ , Typ.  $V_{CE(sat)} = 0.3V$  at  $I_C/I_B = 500mA/50mA$ .  
Optimal for low Voltage operation.
- Complementary to BTA1036L3.

### Symbol



### Outline



### Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	$V_{CB0}$	75	V
Collector-Emitter Voltage	$V_{CEO}$	40	V
Emitter-Base Voltage	$V_{EBO}$	6	V
Collector Current	$I_C$	0.6	A
Power Dissipation (Tc=25°C)	$P_D$	5	W
Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-55~+150	°C


**Characteristics (Ta=25°C)**

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV <sub>CBO</sub>	75	-	-	V	I <sub>C</sub> =10μA
BV <sub>CEO</sub>	40	-	-	V	I <sub>C</sub> =10mA
BV <sub>EBO</sub>	6	-	-	V	I <sub>E</sub> =10μA
I <sub>CBO</sub>	-	-	10	nA	V <sub>CB</sub> =60V
I <sub>CEX</sub>	-	-	10	nA	V <sub>CE</sub> =60V, V <sub>BE</sub> =-3V
I <sub>EBO</sub>	-	-	10	nA	V <sub>EB</sub> =3V
*V <sub>CE(sat)1</sub>	-	-	0.5	V	I <sub>C</sub> =380mA, I <sub>B</sub> =10mA
*V <sub>CE(sat)2</sub>	-	-	0.4	V	I <sub>C</sub> =150mA, I <sub>B</sub> =15mA
*V <sub>CE(sat)3</sub>	-	-	0.75	V	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA
*V <sub>BE(sat)1</sub>	0.75	-	0.95	V	I <sub>C</sub> =150mA, I <sub>B</sub> =15mA
*V <sub>BE(sat)2</sub>	-	-	1.2	V	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA
*h <sub>FE1</sub>	35	-	-		V <sub>CE</sub> =1V, I <sub>C</sub> =0.1mA
*h <sub>FE2</sub>	50	-	-		V <sub>CE</sub> =1V, I <sub>C</sub> =1mA
*h <sub>FE3</sub>	75	-	-		V <sub>CE</sub> =1V, I <sub>C</sub> =10mA
*h <sub>FE4</sub>	82	-	390		V <sub>CE</sub> =1V, I <sub>C</sub> =150mA
*h <sub>FE5</sub>	40	-	-		V <sub>CE</sub> =2V, I <sub>C</sub> =500mA
f <sub>T</sub>	300	-	-	MHz	V <sub>CE</sub> =5V, I <sub>C</sub> =20mA, f=100MHz
C <sub>ob</sub>	-	6	-	pF	V <sub>CB</sub> =5V, f=1MHz

\*Pulse Test: Pulse Width ≤380μs, Duty Cycle ≤2%

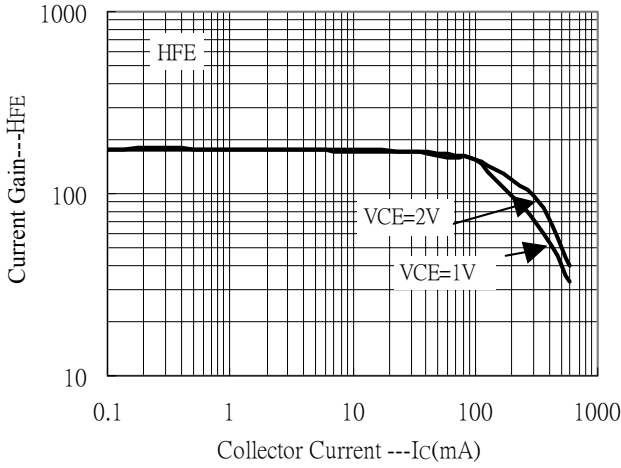
**Classification Of h<sub>FE</sub> 4**

Rank	P	Q	R
Range	82~180	120~270	180~390

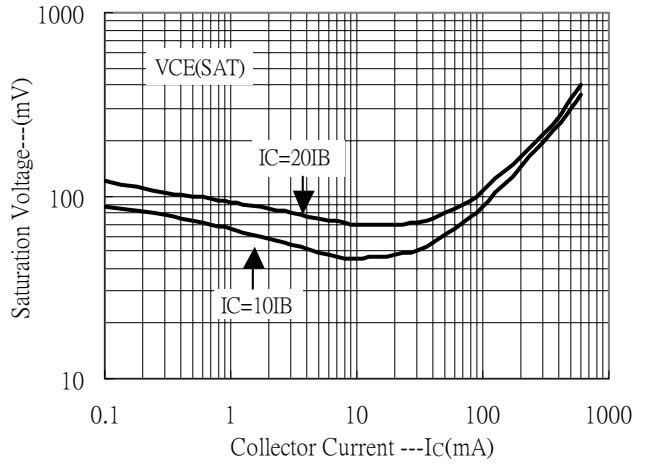


**Characteristic Curves**

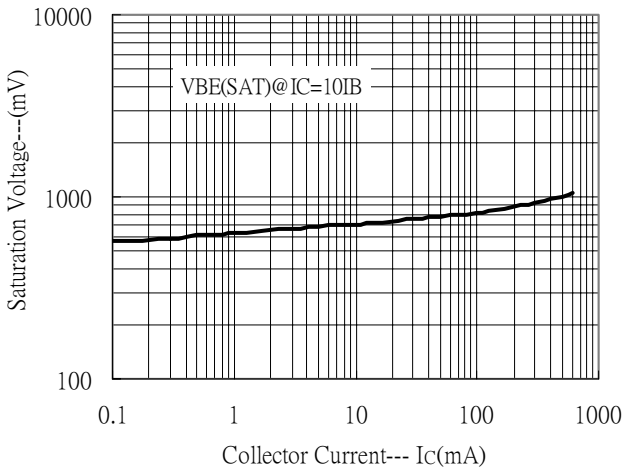
Current Gain vs Collector Current



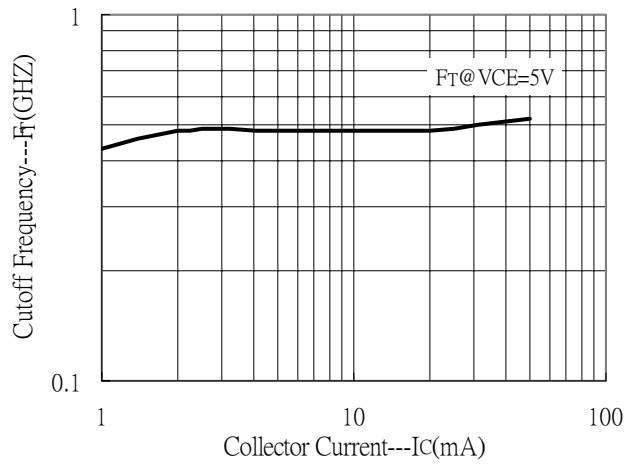
Saturation Voltage vs Collector Current



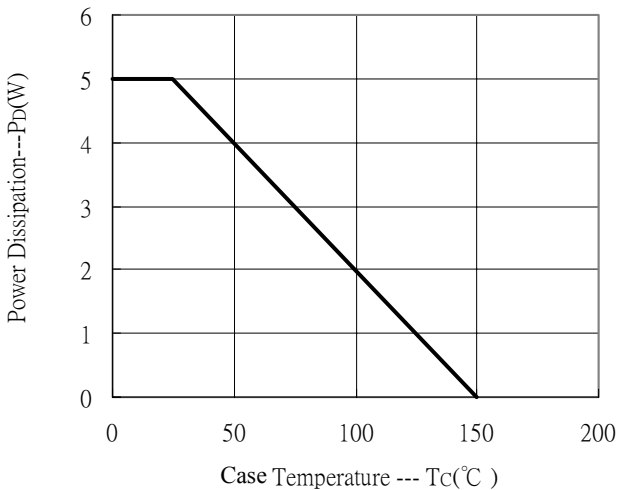
Saturation Voltage vs Collector Current

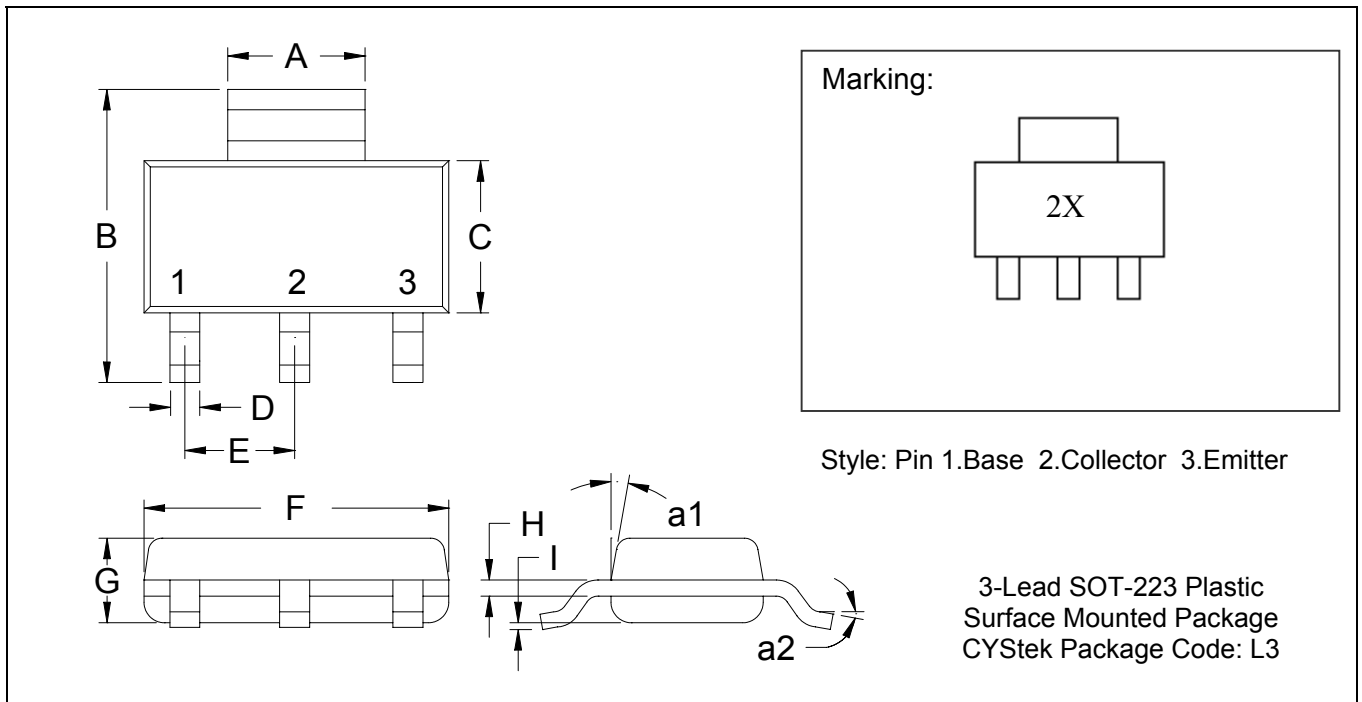


Cutoff Frequency vs Collector Current



Power Derating Curve



**SOT-223 Dimension**


\*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1142	0.1220	2.90	3.10	G	0.0551	0.0709	1.40	1.80
B	0.2638	0.2874	6.70	7.30	H	0.0098	0.0138	0.25	0.35
C	0.1299	0.1457	3.30	3.70	I	0.0008	0.0039	0.02	0.10
D	0.0236	0.0315	0.60	0.80	a1	*13°	-	*13°	-
E	*0.0906	-	*2.30	-	a2	0°	10°	0°	10°
F	0.2480	0.2638	6.30	6.70					

Notes: 1.Controlling dimension: millimeters.

2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.

3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead: 42 Alloy; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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